

In the Claims

Claims 1-6 (canceled).

Claim 7 (original): A physical vapor deposition target, comprising:

at least 30 atom percent cobalt;

at least 10 atom percent silicon; and

one phase comprising cobalt, and not more than 1% of any additional phases comprising cobalt other than said one phase.

Claim 8 (original): The physical vapor deposition target of claim 7, wherein the target is non-magnetic.

Claim 9 (original): The physical vapor deposition target of claim 7, wherein the target comprises no more than 1% of any additional phases which do not comprise cobalt.

Claim 10 (original): The physical vapor deposition target of claim 7 comprising a density that is at least 85% of a theoretical maximum density of the material of the target.

Claim 11 (original): The physical vapor deposition target of claim 7 comprising a density that is at least 90% of a theoretical maximum density of the material of the target.

Claim 12 (original): The physical vapor deposition target of claim 7 comprising a density that is at least 93% of a theoretical maximum density of the material of the target.

Claim 13 (original): The physical vapor deposition target of claim 7 consisting essentially of the cobalt and silicon.

Claim 14 (original): The physical vapor deposition target of claim 7 consisting of the cobalt and silicon.

Claim 15 (original): The physical vapor deposition target of claim 7 consisting essentially of CoSi_2 .

Claim 16 (original): A physical vapor deposition target, comprising:
at least 30 atom percent nickel;
at least 10 atom percent silicon; and
one phase comprising nickel, and not more than 1% of any additional phases comprising nickel other than said one phase.

Claim 17 (original): The physical vapor deposition target of claim 16 comprising a density that is at least 85% of a theoretical maximum density of the material of the target.

Claim 18 (original): The physical vapor deposition target of claim 16 wherein the target comprises less than 1% of any additional phases which do not comprise nickel.

Claim 19 (original): The physical vapor deposition target of claim 16, wherein the target is non-magnetic.

Claim 20 (original): The physical vapor deposition target of claim 16 consisting essentially of the Ni and silicon.

Claim 21 (original): The physical vapor deposition target of claim 16 consisting of the Ni and silicon.

Claim 22 (currently amended): A physical vapor deposition target, comprising:
at least 30 atom percent total of one or more of Co, Ni, Ta, Ti, Pt, and Mo;
at least 10 atom percent silicon;
one phase comprising the one or more of Co, Ni, Ta, Ti, Pt, and Mo and not more than 1% of any additional phases comprising the one or more of Co, Ni, Ta, Ti, Pt, and Mo other than said one phase; and
wherein the target is non-magnetic.

Claim 23 (original): The physical vapor deposition target of claim 22 comprising a density that is at least 85% of a theoretical maximum density of the material of the target.

Claim 24 (original): The physical vapor deposition target of claim 22 wherein the target comprises no more than 1% of any additional phases which do not comprise one or more of Co, Ni, Ta, Ti, Pt and Mo.

Claim 25 (original): The physical vapor deposition target of claim 22 comprising at least 30 atom percent of Ta.

Claim 26 (original): The physical vapor deposition target of claim 22 comprising at least 30 atom percent of Ti.

Claim 27 (original): The physical vapor deposition target of claim 22 comprising at least 30 atom percent of Pt.

Claim 28 (original): The physical vapor deposition target of claim 22 comprising at least 30 atom percent of Mo.

Claim 29 (original): A physical vapor deposition target, comprising:
at least 20 atom percent total of W;
at least 10 atom percent silicon;
one phase comprising WSi_2 and not more than 1% of any additional phases other than said one phase; and
wherein the target is non-magnetic.

Claim 30 (original): The target of claim 29 wherein the W concentration is at least 25 atom percent.